

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Name Paul Timans et al

Serial No. 10/629,400

Filed: July 28, 2003

For: SELECTIV REFLECTIVITY PROCESS CHAMBER  
WITH COSTOMIZED WAVELENGTH RESPONSE  
AND METHOD

Examiner: Not Yet Assigned

Art Group: 2812

Att. Docket No.: MAT-9

Date: December 29, 2003

CERTIFICATE OF MAILING I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner of Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on December 29, 2003.

Signed: 

Jay R Beyer

Commissioner of Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Enclosed is a copy of Information Disclosure Citation Form PTO-1449 together with copies of the documents cited on that form. It is respectfully requested that the cited documents be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made and is not to be construed as an admission that the information cited in this statement is material to patentability.

Pursuant to 37 C.F.R. § 1.97, this Information Disclosure Statement is being submitted under one of the following (as indicated by an "X" to the left of the appropriate paragraph):

X  37 C.F.R. § 1.97(b).

37 C.F.R. § 1.97(c). If so, then enclosed with this Information Disclosure Statement is one of the following:

A certification pursuant to 37 C.F.R. § 1.97(e) or

A check for \$   for the fee under 37 C.F.R. § 1.17(p).

37 C.F.R. § 1.97(d). If so, then enclosed with this Information Disclosure Statement are the following:

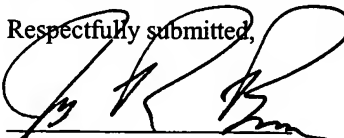
(1) A certification pursuant to 37 C.F.R. § 1.97(e);

(2) A petition requesting consideration of the Information Disclosure Statement; and

(3) Please charge Deposit Account No. 19-1685 (Order No. MAT-9) \$   for the fee under 37 C.F.R. § 1.17(i) for submission of the Information Disclosure Statement. (a duplicate copy of this sheet is enclosed)

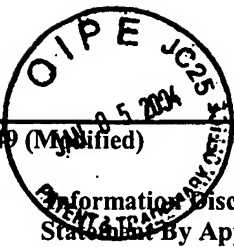
If there are any additional charges, please charge Deposit Account No. 19-1685 (Order No. MAT-9).

Respectfully submitted,



Jay R Beyer

Registration No. 39,907



Form 1449 (Modified)	Atty Docket No. <b>MAT-9</b>	Serial No.: <b>10/629,400</b>
Information Disclosure Statement By Applicant	Applicants: <b>Timans et al</b>	
(Use Several Sheets if Necessary)	Filing Date <b>July 28, 2003</b>	Group <b>2812</b>

#### U.S. Patent Documents

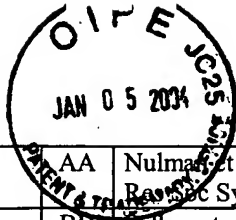
Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
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	B	4,579,080	4/1/1986	Martin et al			
	C	5,561,735	10/1/1996	Camm			
	D	5,971,565	10/26/1999	Zapata et al			
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#### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	O	WO 03/060447 A1	7/24/2003	Canada				

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Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	P	Knutson et al, Modeling Of Radiation Heat Transfer And Wafer Temperatures In A Complex Three-Dimensional Rapid Thermal Processing Chamber, 8/31/1994, 2 <sup>nd</sup> International Rapid Thermal Processing Conference, Monterey California
	Q	Burggraaf, Rapid Wafer Heating: Status 1983, 12/1983, Semiconductor International, pp69-74
	R	Gelpey et al, Process Control for a Rapid Optical Annealing System, 1986, Mat Res Soc Symp Proc, Vol 52, Materials Research Society
	S	Wilson et al, an Overview and Comparison of Rapid Thermal Processing Equipment: A Users Viewpoint, 1986, Mat Res Soc Symp Proc, Vol 52, Materials Research Society
	T	Blake et al, Slip Free Rapid Thermal Processing, 1987, Mat Res Soc Symp Proc, Vol 92, Materials Research Society
	U	Celler et al, Drift of Arsenic in SiO <sub>2</sub> in a Lamp Furnace with a Built-in Temperature Gradient, 1987, Mat Res Soc Symp Proc, Vol 92, Materials Research Society
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	W	Hill et al, Reduced Thermal Processing for ULSI, 1989, Plenum Press, pp 143-180
	X	Kakoschke, Is There a Way to a Perfect Rapid Thermal Processing System?, 1991, Mat Res Soc Symp Proc, Vol 224, Materials Research Society, pp 159-170
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CC	Dilhac et al, Thermal Model for Rapid Thermal Processors: Theory and Applications, 9/8/1993, 1 <sup>st</sup> International Rapid Thermal Processing Conference, Scottsdale, Arizona
DD	Wei et al, Transient Processing of Titanium Silicides in a Non-Isothermal Reactor, 1985, Mat Res Soc Symp Proc, Vol 35, Materials Research Society, pp 465-470
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FF	Dilhac et al, Thermal Modeling of a Wafer in a Rapid Thermal Processor, 11/1995, IEEE Transactions on Semiconductor Manufacturing, Vol 8, No 4, pp 432-439
GG	Henda et al, Investigation of the Thermal Behavior of a RTP Furnace, 8/1995, IEEE Transactions on Semiconductor Manufacturing, Vol 8, No 3, pp 362-365
Examiner	
Date Considered	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.